

# Optimization for Chip Stack in 3D Packaging

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## ISMP 2005

# Optimization of terminal structure for chip stack in 3D packaging

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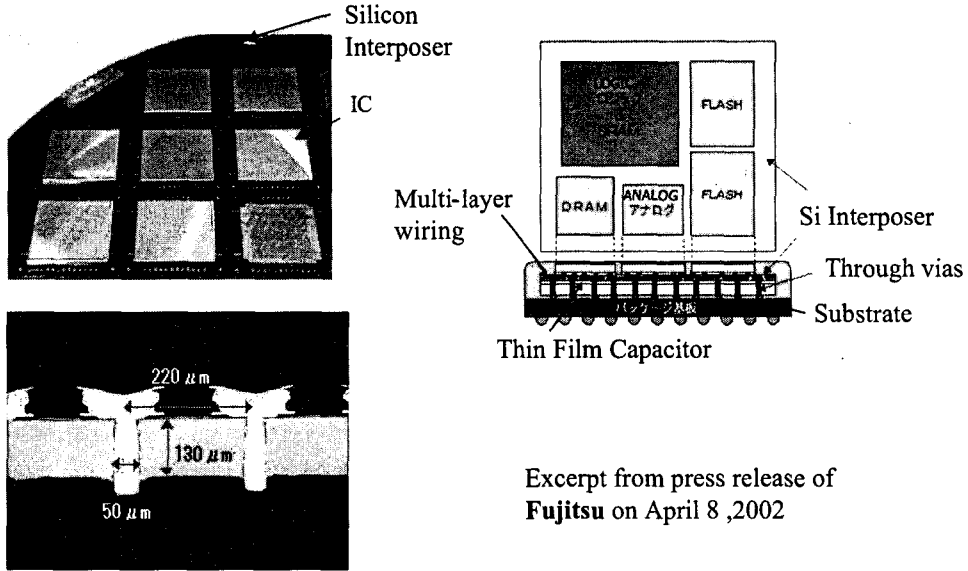
## **1. Introduction**

### **Advantages of 3D packages with Through-Silicon Vias**

1. Extremely small
2. Reduction of the number of parts
3. Good electrical transmission characteristics
4. Possibility of wafer level production
5. Cost reduction

## Applications of the Technology

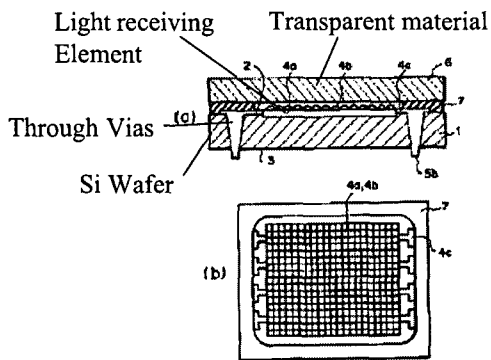
### (1) Silicon Interposer module



Excerpt from press release of  
Fujitsu on April 8, 2002

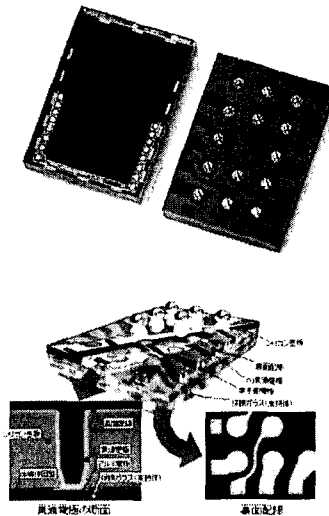
## Applications of the Technology

### (2) CCD Module



2001-35197  
(Patent application laid-open  
disclosure number)

Canon

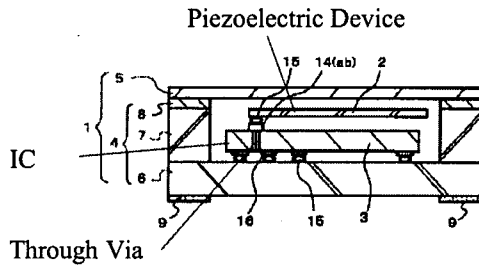


Excerpt from press release of  
ASET on Feb 18, 2004

## Applications of the Technology

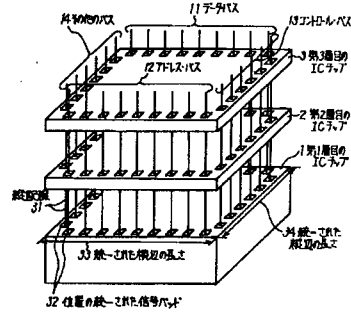
### (3) MEMS complex

### (4) Memory stack



JP3634676

Nihon Dempa Kogyo Co., Ltd



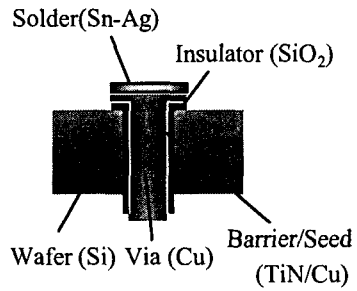
JP2605968

NEC

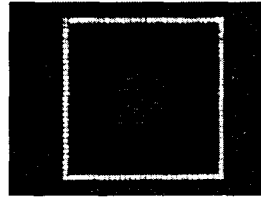
## 2. Model and Process Flow

# Model

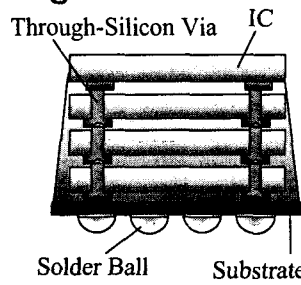
## Through-Silicon via



## Chip



## Package

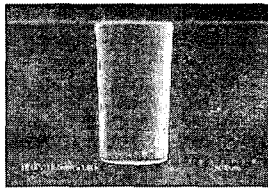
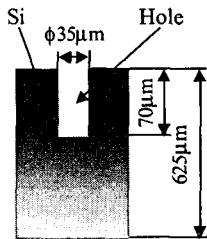


## Specification

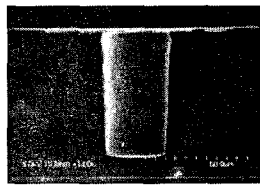
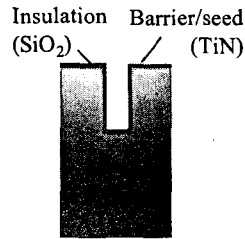
Size	5mm x 5mm
Thickness	45 μm
I/O Count	120
Pitch	150μm
Pad size	120μm
Diameter of via	35μm x 35μm

# Process Flow

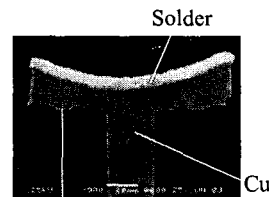
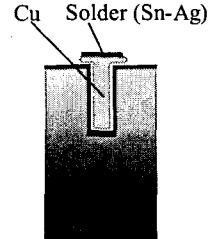
### (1) Hole opening



### (2) Layer forming

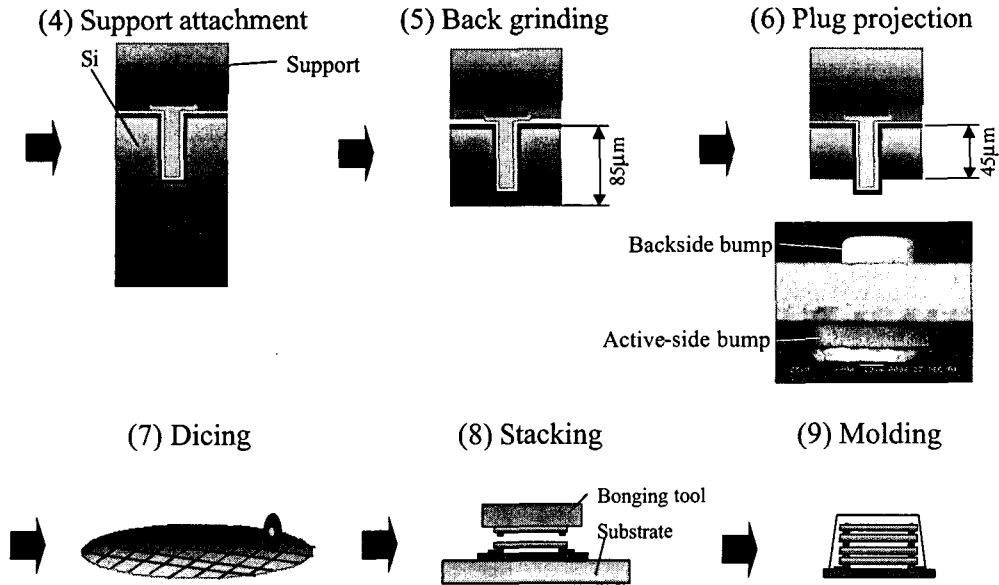


### (3) Cu Filling



Al-Cu Contact area

## Process Flow

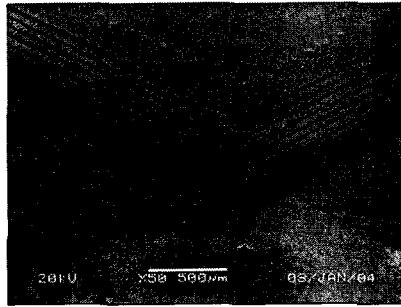


## Features

- No flattening process for active-side terminals
- No insulation layer on the backside of wafer
- Simple process
- Cost reduction



### 3. Optimization for interconnection



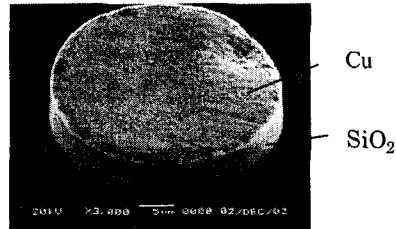
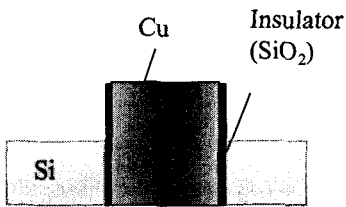
**Specification**

Package Thickness	810μm
IC Size	5mm x 5mm
I/O Count	120
Pitch	150μm

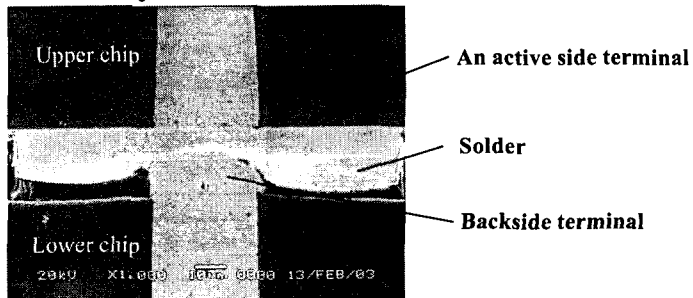
10-layer chip stack

### Solder Drop

**Initial structure of backside terminals**

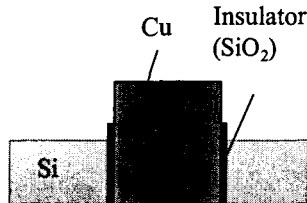


**Solder drop at solder joints**



## Modification

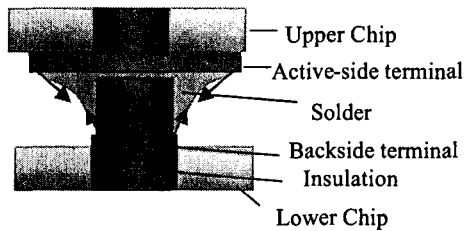
The modified structure of backside terminals



Verification using test chips

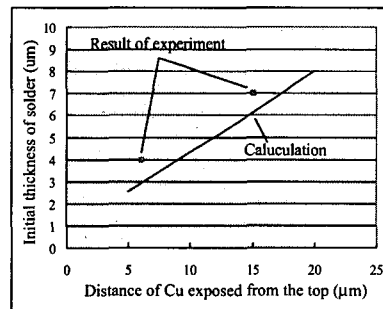
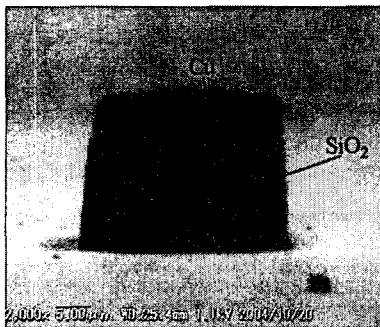


Solder shape and directions of surface tensions



## Result of the Modification

Modified backside terminal Estimation of the amount of solder



Solder Joint

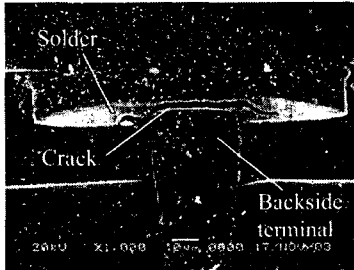


Specification of modified terminals

Height	25μm
Distance of Cu exposure	7μm
Initial thickness of solder	4μm

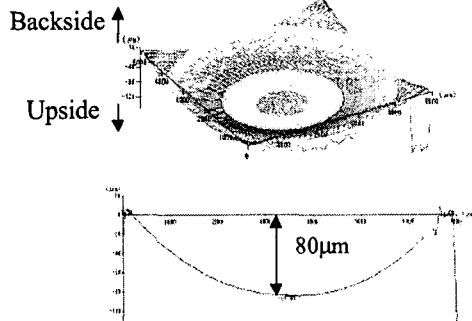
## Crack of Solder Joints

### Crack of solder joint



### Cause

#### Warpage of the chip

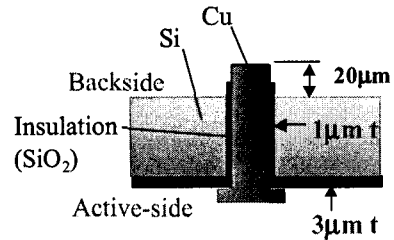
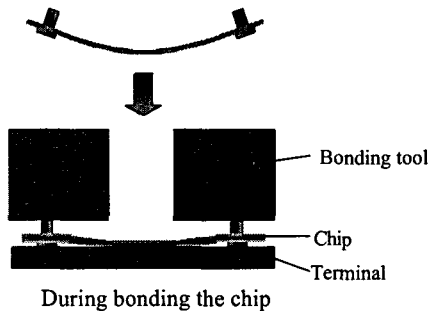


Height change along a diagonal line of the chip

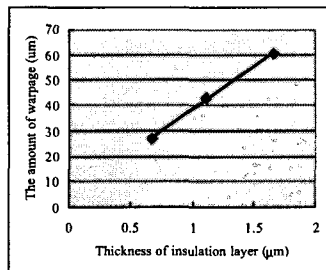
The result of 3-Dimensional measurement

## The cause of warpage

Why the crack occurred? Insulation on the surface of the chip



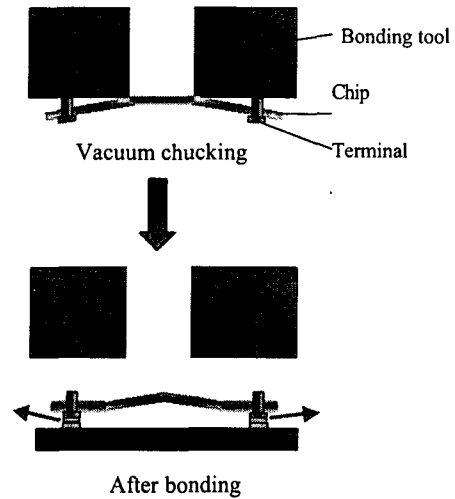
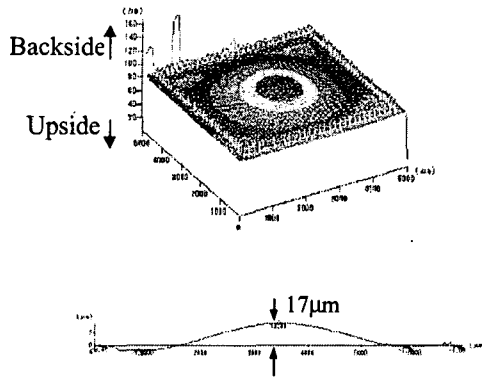
### Relation between insulation thickness and warpage



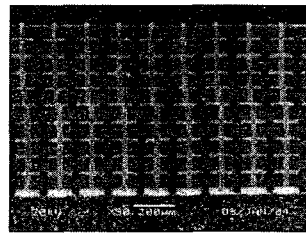
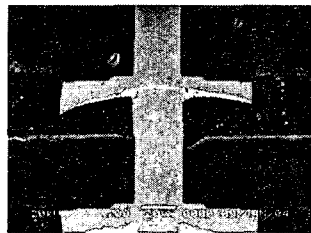
## Effect of Vacuum Chucking

Warpage of bonded chips

Effect of vacuum chucking



## Summary of the Section



Problems	Causes	Measures
Solder Drop	Shortage of constraints of melting solder	Cu exposition on the sidewall of the backside bumps
Crack of solder joints	Warpage of chips Vacuum Chucking	Reduction of thickness of insulation on the surface Elimination of vacuum chucking during bonding

## 4. Performance

### Thermal Cycle Test

Test Condition -55↔125degrees

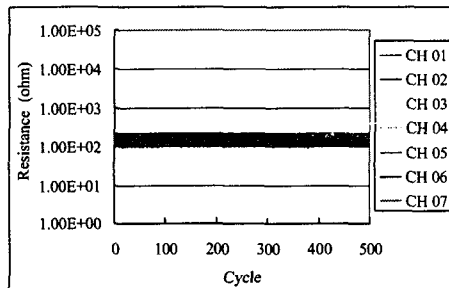
Period 40 min

Result No failures after 500cycles (n=14)

#### Specimen

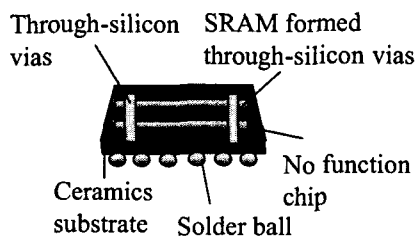
Package	
The number of layer	4
Material of Substrate	Ceramics
The number of specimens	7
2 types of resin evaluated	

#### Transition of resistance



## Verification of Normal Operation

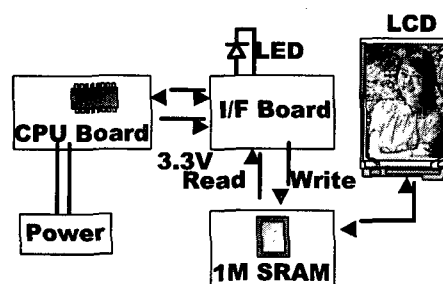
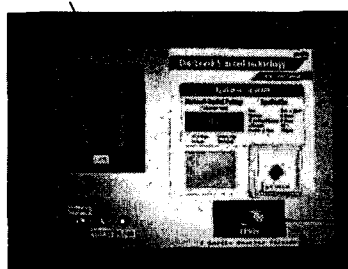
### SRAM Package



### Specification

<b>Package</b>	
Size	7mm x 8mm
I/O Count	48
Ball pitch	0.75mm
Number of layer	2
<b>IC</b>	
Size	6mm x 7mm
I/O Count	48
Thickness	0.05mm

### Apparatus



## 5. Conclusions

- Simple process flow was realized with the modification of structure of back side terminals.
- Cu exposure on the sidewall of backside terminals was essential to prevent solder from dropping.
- Decreasing the deformation of chips during bonding was essential. Following measures are effective.
  - Reduction of the thickness of insulation layer
  - Eliminating vacuum chucking during bonding
- Good thermal cycle performance was verified.
- Normal operation was confirmed by using SRAM where through -Si vias were formed.

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